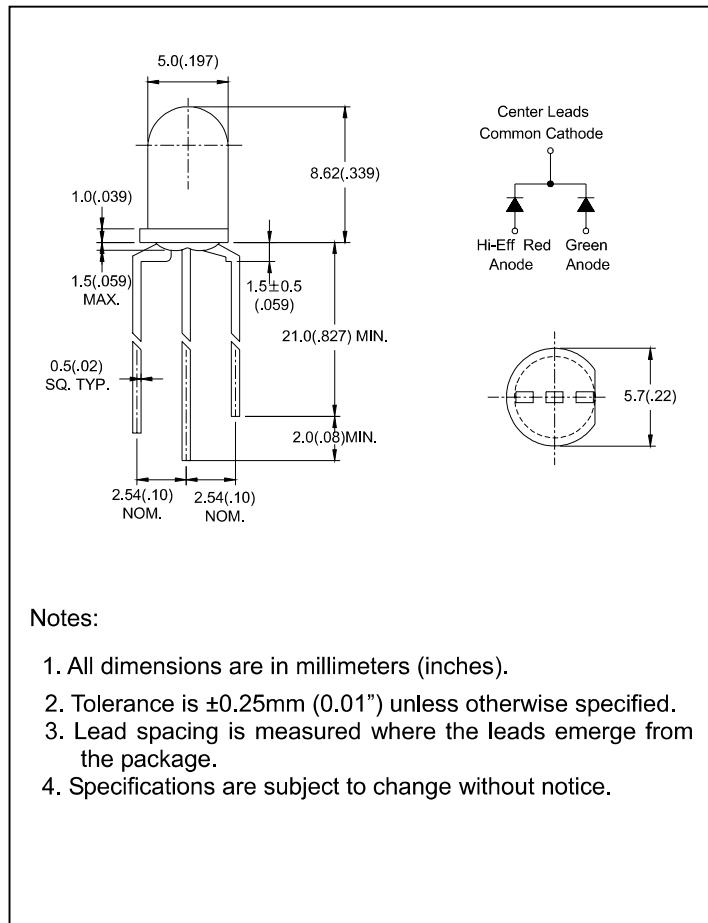


● Features:

1. Chip material: GaAsP/GaP (Red) and GaP/GaP (Green)
2. Emitted color : Hi-Eff Red and Green
3. Lens Appearance : White Diffused
4. Low power consumption.
5. High efficiency.
6. Versatile mounting on P.C. Board or panel.
7. Low current requirement.
8. 5mm diameter package
9. This product don't contained restriction substance, compliance ROHS standard.

● Package Dimensions:



● Applications:

1. TV set
2. Monitor
3. Telephone
4. Computer
5. Circuit board

● Absolute Maximum Ratings($T_a=25^\circ\text{C}$)

Parameter	Symbol	Hi-Eff Red	Green	Unit
Power Dissipation	P _d	80	80	mW
Forward Current	I _F	30	30	mA
Peak Forward Current ^{*1}	I _{FP}	150	150	mA
Reverse Voltage	V _R		5	V
Operating Temperature	T _{opr}		-40°C~85	
Storage Temperature	T _{stg}		-40°C~100°C	
Soldering Temperature	T _{sol}		260°C (for 5 seconds)	

^{*1}Condition for I_{FP} is pulse of 1/10 duty and 0.1msec width.

● Electrical and optical characteristics(Ta=25°C)

Parameter	Symbol	Condition	Color	Min.	Typ.	Max.	Unit
Forward Voltage	V _F	I _F =20mA	Hi-Eff Red Green	-	2.1 2.2	2.6 2.6	V
Luminous Intensity	I _V	I _F =20mA	Hi-Eff Red Green	-	45 45	-	mcd
Reverse Current	I _R	V _R =5V	Hi-Eff Red Green	-	-	100	μA
Peak Wave Length	λ _p	I _F =20mA	Hi-Eff Red Green	-	640 568	-	nm
Dominant Wave Length	λ _d	I _F =20mA	Hi-Eff Red Green	617 560	- -	638 576	nm
Spectral Line Half-width	Δ λ	I _F =20mA	Hi-Eff Red Green	-	40 30	-	nm
Viewing Angle	2θ _{1/2}	I _F =20mA	Hi-Eff Red Green	-	50	-	deg

● Typical Electro-Optical Characteristics Curves

Fig.1 Relative intensity vs. Wavelength

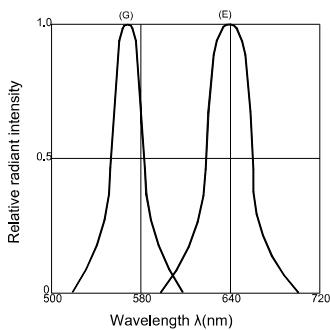


Fig.2 Forward current derating curve vs. Ambient temperature

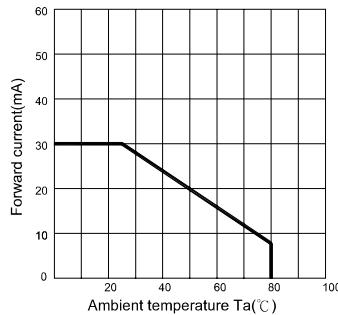


Fig.3 Forward current vs. Forward voltage

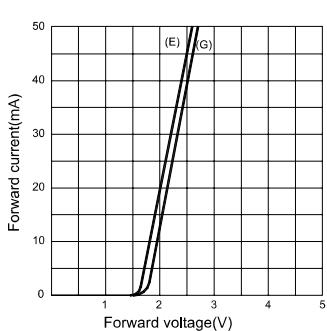


Fig.4 Relative luminous intensity vs. Ambient temperature

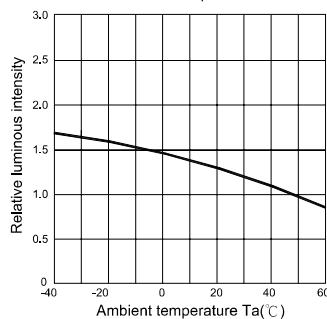


Fig.5 Relative luminous intensity vs. Forward current

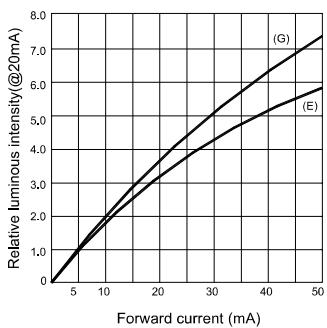


Fig.6 Radiation diagram

